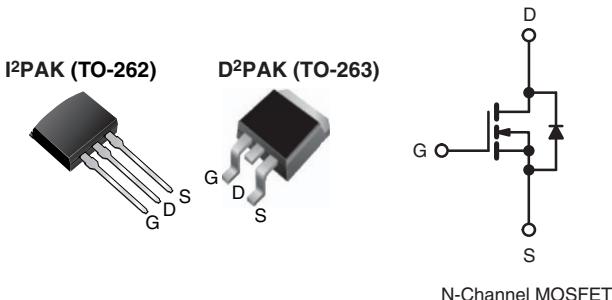


Power MOSFET

PRODUCT SUMMARY	
V_{DS} (V)	60
$R_{DS(on)}$ (Ω)	$V_{GS} = 10$ V 0.018
Q_g (Max.) (nC)	110
Q_{gs} (nC)	29
Q_{gd} (nC)	36
Configuration	Single



FEATURES

- Advanced process technology
- Surface mount (IRFZ48S, SiHFZ48S)
- Low-profile through-hole (IRFZ48L, SiHFZ48L)
- 175 °C operating temperature
- Fast switching
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS*
Available
HALOGEN FREE
Available

Note

* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non-RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details.

DESCRIPTION

Third generation power MOSFETs from Vishay utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The D²PAK is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D²PAK is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2 W in a typical surface mount application.

The through-hole version (IRFZ48L, SiHFZ48L) is available for low-profile applications.

ORDERING INFORMATION		
Package	D ² PAK (TO-263)	I ² PAK (TO-262)
Lead (Pb)-free and halogen-free	SiHFZ48S-GE3	SiHFZ48L-GE3
Lead (Pb)-free	IRFZ48SPbF	-

Note

a. See device orientation.

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ^f	I_D	50	A
		50	
Pulsed Drain Current ^{a, e}	I_{DM}	290	W/°C
Linear Derating Factor		1.3	
Single Pulse Avalanche Energy ^{b, e}	E_{AS}	100	mJ
Maximum Power Dissipation	P_D	190	W
		3.7	
Peak Diode Recovery dV/dt ^{c, e}	dV/dt	4.5	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +175	°C
Soldering Recommendations (Peak temperature) ^d	for 10 s	300	

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = 25$ V, Starting $T_J = 25$ °C, $L = 22$ μ H, $R_g = 25$ Ω , $I_{AS} = 72$ A (see fig. 12).
- $I_{SD} \leq 72$ A, $dI/dt \leq 200$ A/ μ s, $V_{DD} \leq V_{DS}$, $T_J \leq 175$ °C.
- 1.6 mm from case.
- Uses IRFZ48, SiHFZ48 data and test conditions.
- Calculated continuous current based on maximum allowable junction temperature.

THERMAL RESISTANCE RATINGS

PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient (PCB mount) ^a	R_{thJA}	-	40	$^{\circ}\text{C} / \text{W}$
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.8	

Note

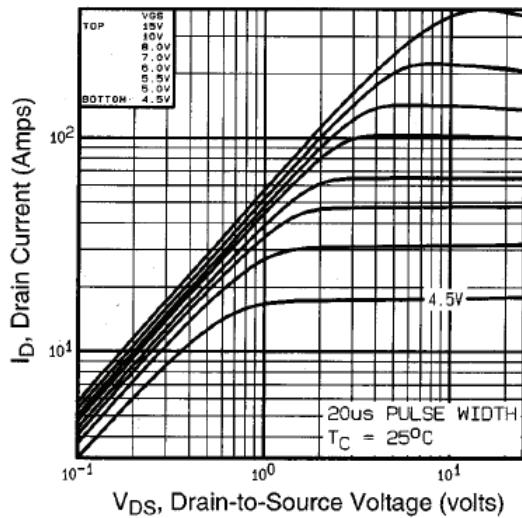
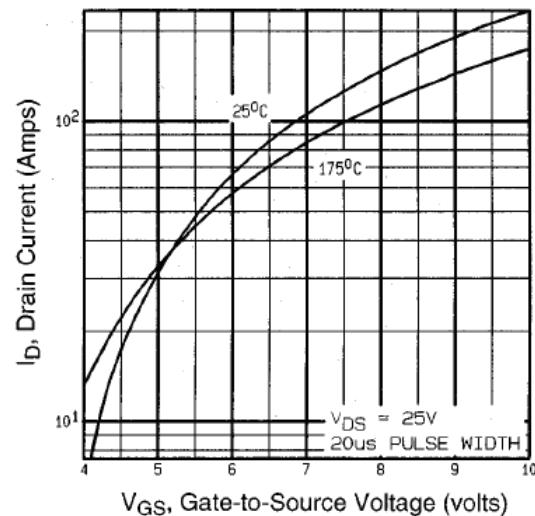
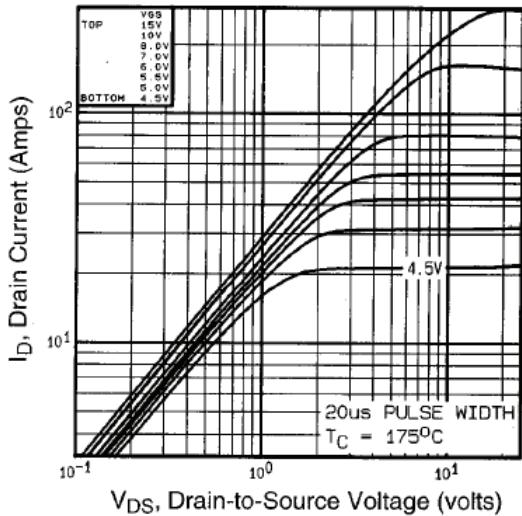
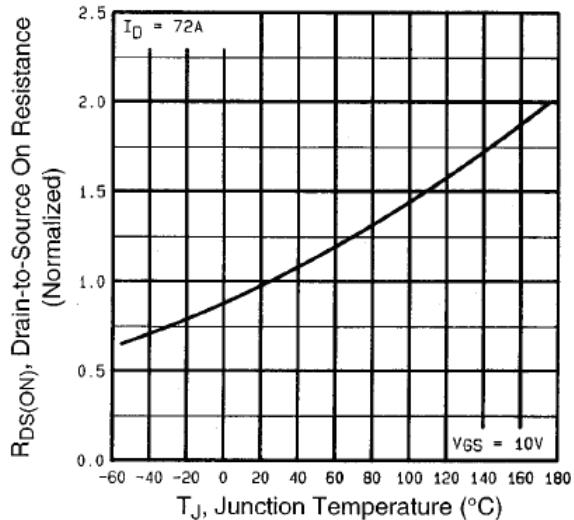
- a. When mounted on 1" square PCB (FR-4 or G-10 material).

SPECIFICATIONS ($T_J = 25 \text{ }^{\circ}\text{C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0$	$I_D = 250 \mu\text{A}$	60	-	-	V	
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25 \text{ }^{\circ}\text{C}$, $I_D = 1 \text{ mA}$ ^c		-	0.060	-	$\text{V}/\text{^{\circ}C}$	
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$		2.0	-	4.0	V	
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 60 \text{ V}$, $V_{GS} = 0 \text{ V}$		-	-	25	μA	
		$V_{DS} = 48 \text{ V}$, $V_{GS} = 0 \text{ V}$, $T_J = 150 \text{ }^{\circ}\text{C}$		-	-	250		
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$	$I_D = 43 \text{ A}$ ^b	-	-	0.018	Ω	
Forward Transconductance	g_{fs}	$V_{DS} = 25 \text{ V}$, $I_D = 43 \text{ A}$ ^b		27	-	-	S	
Dynamic								
Input Capacitance	C_{iss}	$V_{GS} = 0 \text{ V}$, $V_{DS} = 25 \text{ V}$, $f = 1.0 \text{ MHz}$, see fig. 5 ^c		-	2400	-	pF	
Output Capacitance	C_{oss}			-	1300	-		
Reverse Transfer Capacitance	C_{rss}			-	190	-		
Total Gate Charge	Q_g	$V_{GS} = 10 \text{ V}$	$I_D = 72 \text{ A}$, $V_{DS} = 48 \text{ V}$, see fig. 6 and 13 ^{b, c}	-	-	110	nC	
Gate-Source Charge	Q_{gs}			-	-	29		
Gate-Drain Charge	Q_{gd}			-	-	36		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 30 \text{ V}$, $I_D = 72 \text{ A}$, $R_g = 9.1 \text{ } \Omega$, $R_D = 0.34 \text{ } \Omega$, see fig. 10 ^{b, c}		-	8.1	-	ns	
Rise Time	t_r			-	250	-		
Turn-Off Delay Time	$t_{d(off)}$			-	210	-		
Fall Time	t_f			-	250	-		
Internal Source Inductance	L_S	Between lead, and center of die contact		-	7.5	-	nH	
Drain-Source Body Diode Characteristics								
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode		-	-	50 ^c	A	
Pulsed Diode Forward Current ^a	I_{SM}			-	-	290		
Body Diode Voltage	V_{SD}	$T_J = 25 \text{ }^{\circ}\text{C}$, $I_S = 72 \text{ A}$, $V_{GS} = 0 \text{ V}$ ^b		-	-	2.0	V	
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25 \text{ }^{\circ}\text{C}$, $I_F = 72 \text{ A}$, $dl/dt = 100 \text{ A}/\mu\text{s}$ ^{b, c}		-	120	180	ns	
Body Diode Reverse Recovery Charge	Q_{rr}			-	500	800	μC	
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)						

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
b. Pulse width $\leq 300 \mu\text{s}$; duty cycle $\leq 2 \%$.
c. Uses IRFZ48/SiHFZ48 data and test conditions.
d. Calculated continuous current based on maximum allowable junction temperature.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Fig. 1 - Typical Output Characteristics

Fig. 3 - Typical Transfer Characteristics

Fig. 2 - Typical Output Characteristics

Fig. 4 - Normalized On-Resistance vs. Temperature

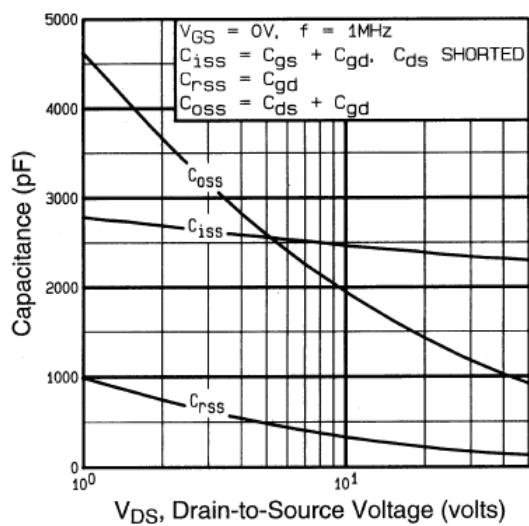


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

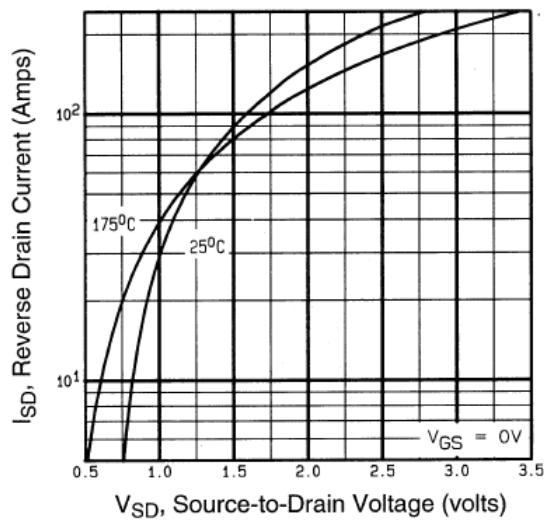


Fig. 7 - Typical Source-Drain Diode Forward Voltage

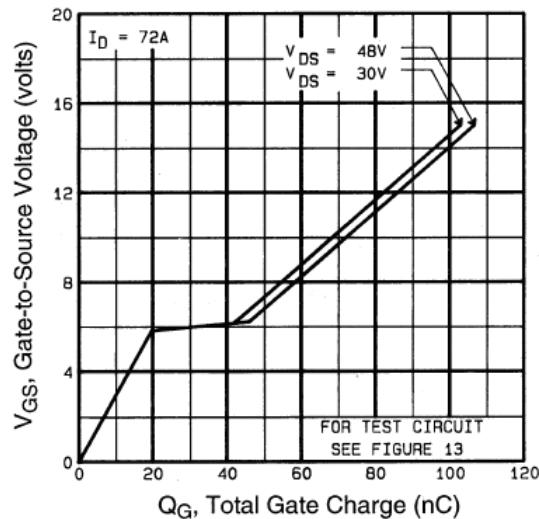


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage

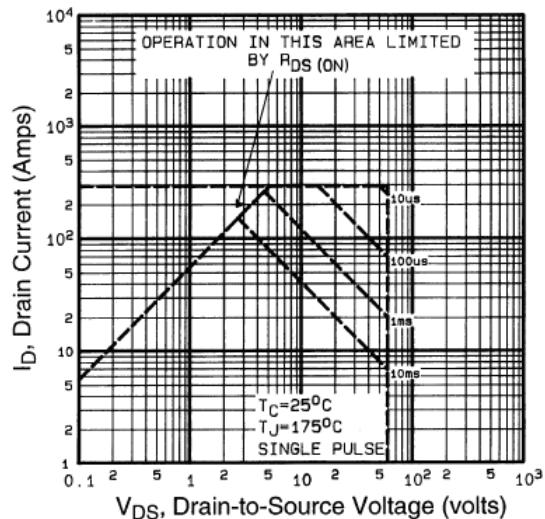
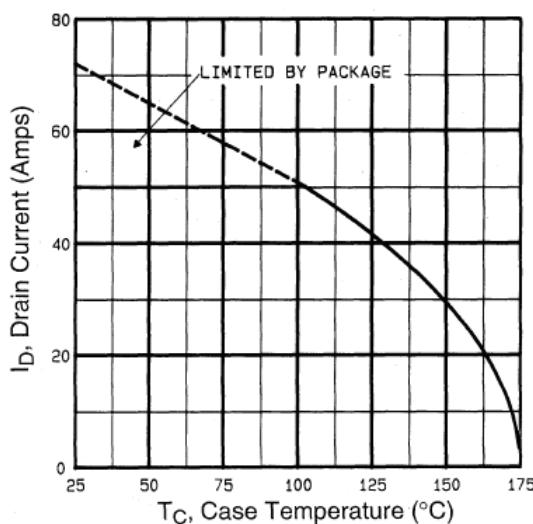
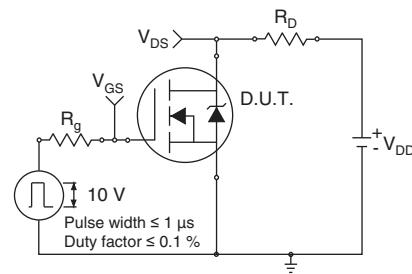
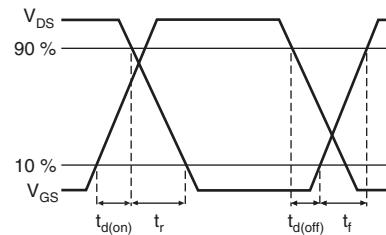
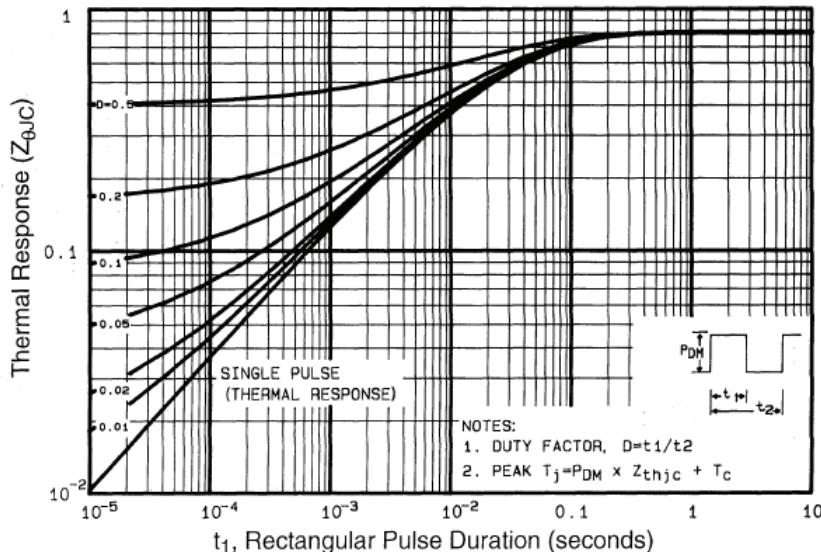
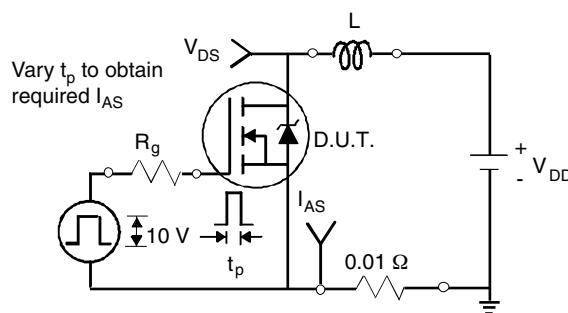
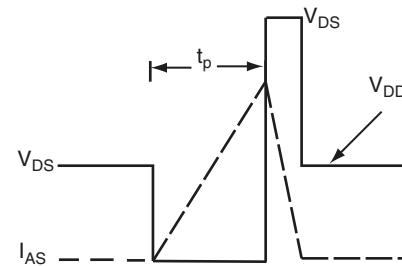
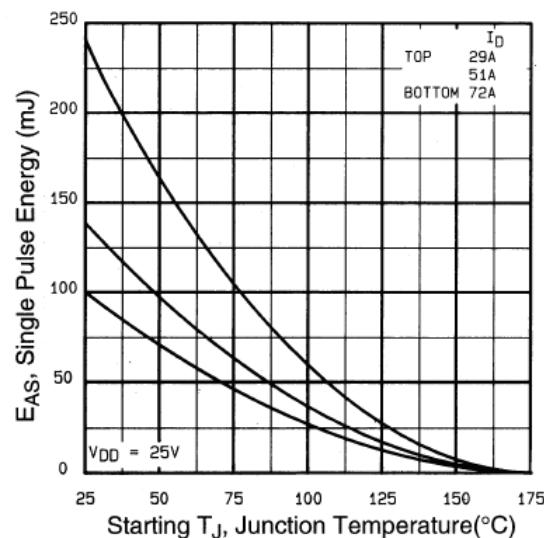
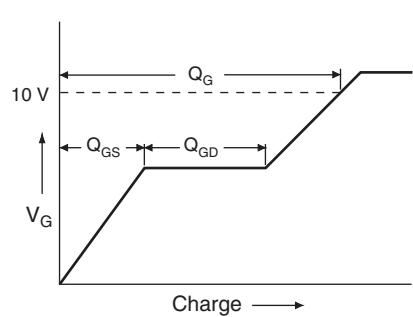
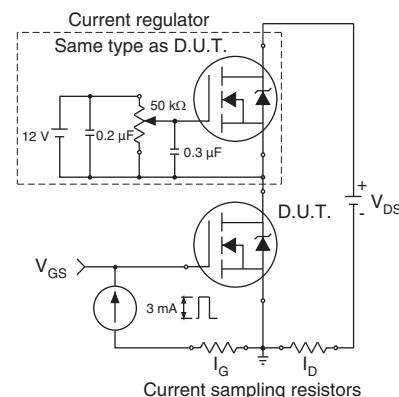
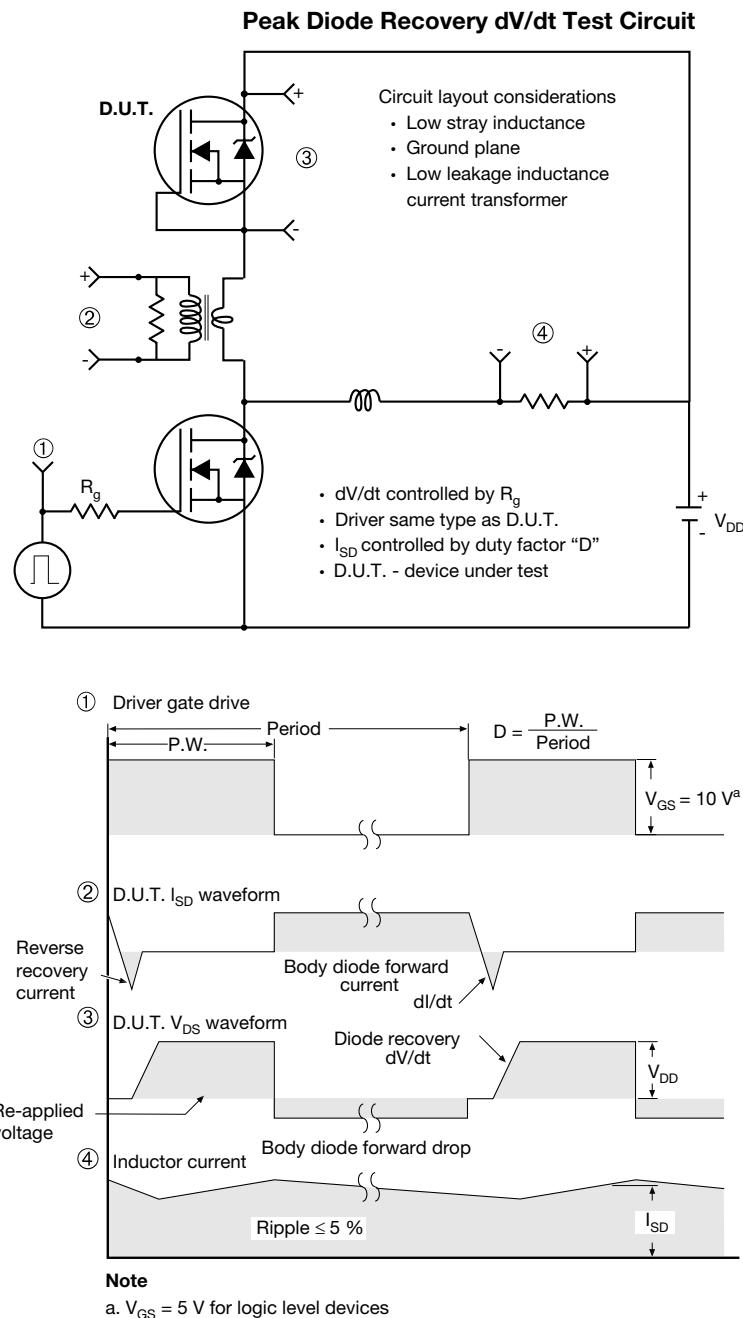


Fig. 8 - Maximum Safe Operating Area

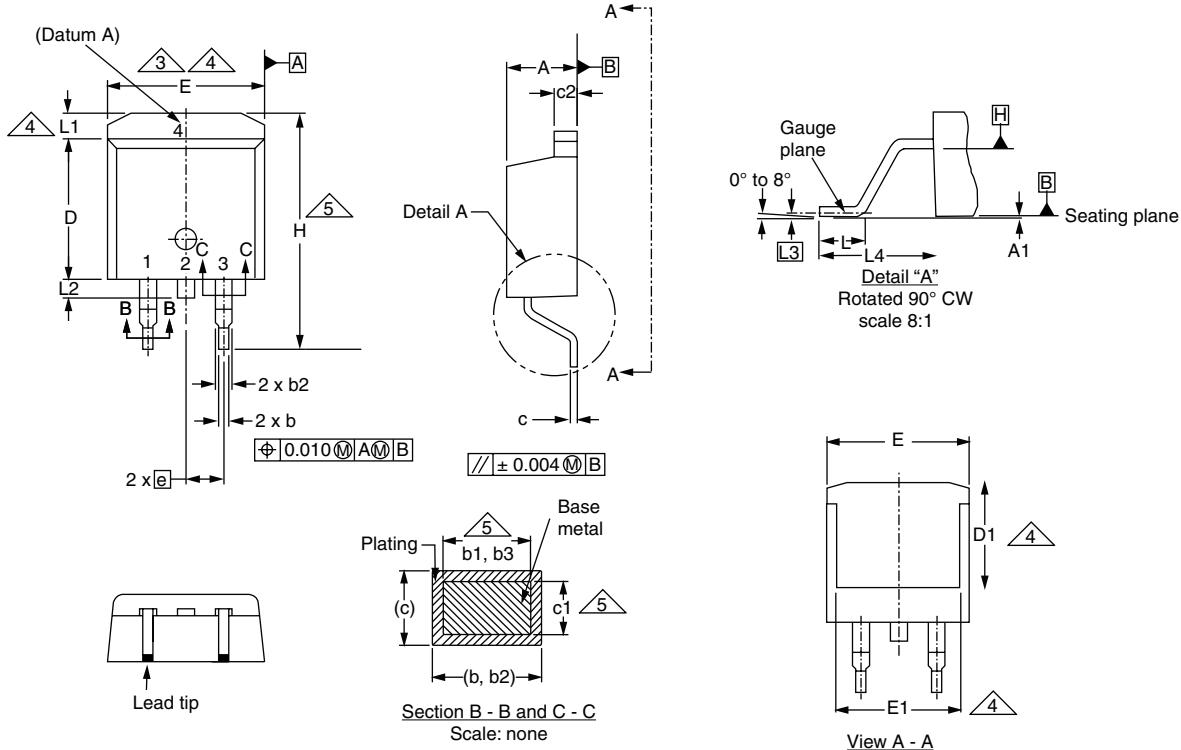

Fig. 9 - Maximum Drain Current vs. Case Temperature

Fig. 10a - Switching Time Test Circuit

Fig. 10b - Switching Time Waveform

Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

Fig. 12a - Unclamped Inductive Test Circuit

Fig. 12b - Unclamped Inductive Waveforms


Fig. 12c - Maximum Avalanche Energy vs. Drain Current

Fig. 13a - Maximum Avalanche Energy vs. Drain Current

Fig. 13b - Gate Charge Test Circuit


Fig. 14 - For N-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?90377.

TO-263AB (HIGH VOLTAGE)



	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	0.00	0.25	0.000	0.010
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
c	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065
D	8.38	9.65	0.330	0.380

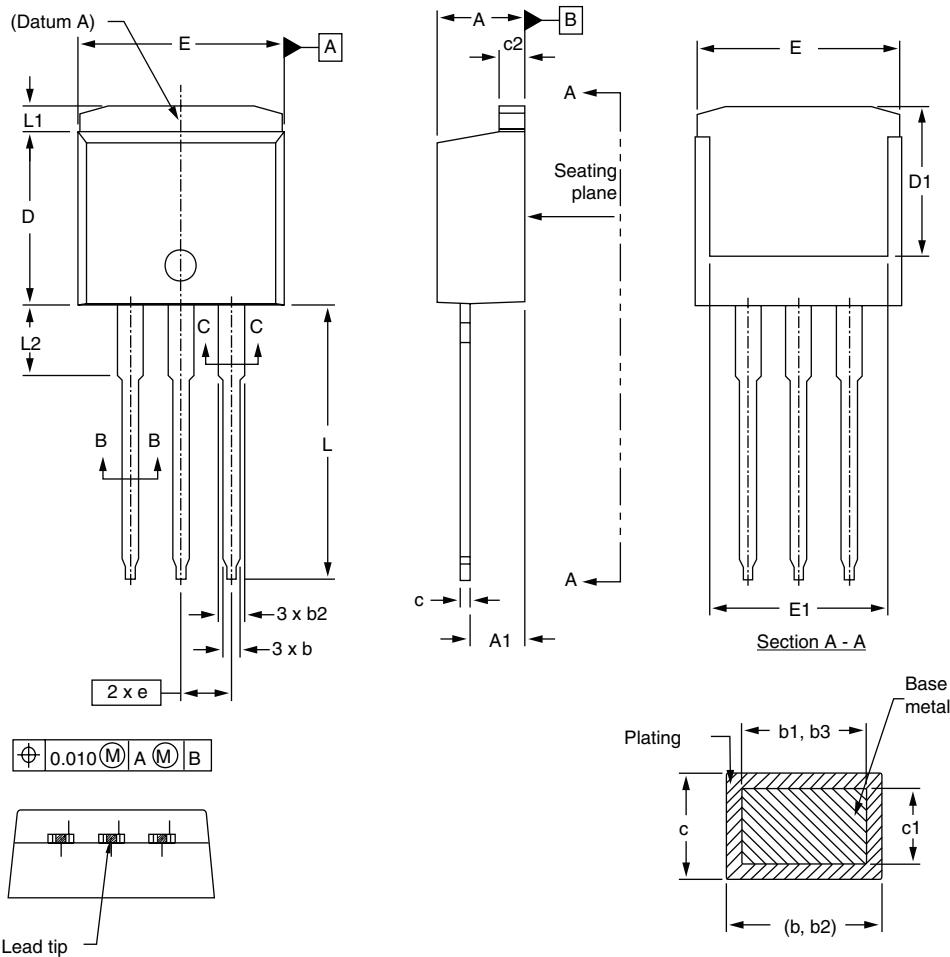
	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	-	1.65	-	0.066
L2	-	1.78	-	0.070
L3	0.25 BSC		0.010 BSC	
L4	4.78	5.28	0.188	0.208

Notes

- Notes**

 1. Dimensioning and tolerancing per ASME Y14.5M-1994.
 2. Dimensions are shown in millimeters (inches).
 3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body at datum A.
 4. Thermal PAD contour optional within dimension E, L1, D1 and E1.
 5. Dimension b1 and c1 apply to base metal only.
 6. Datum A and B to be determined at datum plane H.
 7. Outline conforms to JEDEC outline TO-263AB.

I²PAK (TO-262) (HIGH VOLTAGE)



Section B - B and C - C

Scale: None

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.06	4.83	0.160	0.190
A1	2.03	3.02	0.080	0.119
b	0.51	0.99	0.020	0.039
b1	0.51	0.89	0.020	0.035
b2	1.14	1.78	0.045	0.070
b3	1.14	1.73	0.045	0.068
c	0.38	0.74	0.015	0.029
c1	0.38	0.58	0.015	0.023
c2	1.14	1.65	0.045	0.065

ECN: S-82442-Rev. A, 27-Oct-08

DWG: 5977

Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outmost extremes of the plastic body.
3. Thermal pad contour optional within dimension E, L1, D1, and E1.
4. Dimension b1 and c1 apply to base metal only.

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D	8.38	9.65	0.330	0.380
D1	6.86	-	0.270	-
E	9.65	10.67	0.380	0.420
E1	6.22	-	0.245	-
e	2.54 BSC		0.100 BSC	
L	13.46	14.10	0.530	0.555
L1	-	1.65	-	0.065
L2	3.56	3.71	0.140	0.146

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